

FORM PTO 1449 (modified)  U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE  LIST OF REFERENCES CITED BY APPLICANT(S) (Use several sheets if necessary)		ATTY DOCKET NO. <b>03500.013395.2</b>		APPLICATION NO. <b>Div. of 09/839,891</b>	
APPLICANT <b>KEISHI SAITO ET AL.</b>		FILING DATE <b>H rewith</b>		GROUP <b>NYA</b>	

  

U.S. PATENT DOCUMENTS							
*EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE	
M	4,600,801	7/15/86	Guha et al.	136	249		
	4,609,771	9/2/86	Guha et al.	136	249		
	4,775,425	10/4/88	Guha et al.	136	249		
	5,486,237	1/23/96	Sano et al.	136	258		
	5,720,827	2/24/98	Simmons	136	250		
	5,851,904	12/22/98	Schwarz et al.	438	482		
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L	6,013,544	1/11/00	Makita et al.	438	166		

  

FOREIGN PATENT DOCUMENTS							
DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION YES/NO/ OR ABSTRACT		
0 675 551	10/4/95	Europe					
43 33 416	4/6/95	Germany					

  

OTHER DOCUMENT(S) (Including Author, Title, Date, Pertinent Pages, Etc.)	
<div style="text-align: center;">J</div>	J. Meier, et al., "Towards High Efficiency Thin Film Silicon Solar Cells With The 'Micromorph' Concept", Solar Energy Materials and Solar Cells, vol. 49, pp. 35-44 (1997).
<div style="text-align: center;">J</div>	J. Yi, et al., "Amorphous and Micro-Crystalline Silicon for Photovoltaic Application", Proc. of the Photovoltaic Spec. Conf., vol. 23, pp. 977-980 (1993).
<div style="text-align: center;">J</div>	J. Meier, et al., "On The Way Towards High Efficiency Thin Film Silicon Solar Cells By The Micromorph Concept", Mat. Res. Soc. Symp. Proc., vol. 420, pgs. 3-14 (1996).
<div style="text-align: center;">A</div>	A. Matsuda, "Structural Study on Amorphous-Microcrystalline Mixed-Phase Si:H Films", Jap. J. Appl. Phys., vol. 20, no. 6, pgs. L439-L442 (1981).
<div style="text-align: center;">A</div>	A. Matsuda, et al., "Boron Doping of Hydrogenated Silicon Thin Films", Jap. J. Appl. Phys., vol. 20, no. 3, pgs. L183-L186 (1981).
<div style="text-align: center;">A</div>	A. Matsuda, et al. "Electrical and Structural Properties of Phosphorous-Doped Glow-Discharge Si: F: H and Si:H Films", Jap. J. Appl. Phys., vol. 19, no. 6, pgs. L305-L308 (1980).
<div style="text-align: center;">S</div>	S. Usui, et al., "Properties of Heavily Doped GD-Si With Low Resistivity", Journal of Non-Crystalline Solids, vol. 34, no. 1, pgs. 1-11 (1979).

  

EXAMINER	DATE CONSIDERED
	3/18/05

\*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

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GROUP <div style="text-align: center;"><b>NYA</b></div>			

  

U.S. PATENT DOCUMENTS							
*EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE (IF APPROPRIATE)	
/	6,020,224	2/1/00	Shimogaichi et al.	438	158		
/	6,027,987	2/22/00	Yamazaki et al.	438	486		
P	6,033,940	3/7/00	Jinda	438	151		
/	6,180,870	1/30/01	Sano et al.	136	258		

  

FOREIGN PATENT DOCUMENTS							
*EXAMINER INITIAL	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION YES/NO/ OR ABSTRACT	
/	1175095A	3/4/98	China				

  

OTHER DOCUMENT(S) (Including Author, Title, Date, Pertinent Pages, Etc.)	

  

EXAMINER	DATE CONSIDERED
	3/15/08

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